

T-31-01

General Purpose Transistors

HXTR-3001 Chip

Technical Data

**HXTR-3101, TX and TXV
2N6838 (HXTR-3103, TX
and TXV)
HSMX-3131
HSMX-3151**

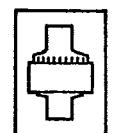
Features

- High Gain
15 dB Typical $|S_{21E}|^2$ at 1 GHz
- High Output Power
21 dBm P_{1dB} Typical at 1 GHz
- Low Noise Figure
1.5 dB Typical at 1 GHz
- Large Gold Bonding Pads
- Available in Low Cost Hermetic and Surface Mount Packages

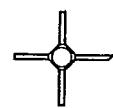
Recommended Die Attach and Bonding Procedures

Eutectic Die Attach at a stage temperature of $410 \pm 10^\circ\text{C}$ under an N_2 ambient. Chip should be lightly scrubbed using a tweezers or collet and eutectic should flow within five seconds.

Thermocompression Wire Bond at a stage temperature of $310 \pm 10^\circ\text{C}$, using a tip force of 30 ± 5 grams with 0.7 or 1.0 mil gold wire. A one mil minimum wire clearance at the passivation edge is recommended. (Ultrasonic bonding is not recommended.)



Generic Chip
HXTR-3001



HPAC-100X

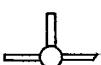
Part No.	Marking "X"
HXTR-3101	U
2N6838 (HXTR-3103)	T



SOT-23
HSMX-3131



SOT-143
HSMX-3151



HXTR-3185
HXTR-3186

Description

The HXTR-3001 is a low cost NPN silicon bipolar transistor chip designed for high gain and wide dynamic range at VHF, UHF, and microwave frequencies. The chip is silicon nitride passivated, and is provided with large gold bonding pads for ease of use in most hybrid applications.

The HXTR-3001 is available in several package styles. The HXTR-3101 and 2N6838 (HXTR-3103) are supplied in the HPAC-100X, a rugged low cost metal/ceramic package capable of meeting the environmental requirements of MIL-S-19500 and the test requirements of MIL-STD-750/883.

The HSMX-3131 and HSMX-3151 are the low cost plastic package versions that are supplied in the SOT-23 and SOT-143 surface mount packages respectively.

The HXTR-3001 chip is also offered in an 85-mil micro-plastic package with copper leads as the HXTR-3185 and HXTR-3186 (bent lead version). These devices replace the 100-mil micro-plastic HXTR-3121 part with alloy 42 leads.

Note: See the Package Outline section, page 16-7, for complete dimensions.

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Electrical Specifications (HXTR-3001, HXTR-3101, HXTR-3103)

Symbol	Parameters and Test Conditions	Test Method MIL-STD-750	Units	HXTR-3001 ^(a)			HXTR-3101 ^(a)			HXTR-3103 ^(a)		
				Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
BV_{CEO}^*	Collector-Base Breakdown Voltage at $I_c = 100 \mu A$	3001*	V				30			30		
BV_{CEO}	Collector-Emitter Breakdown Voltage at $I_c = 10 \text{ mA}$	3001*	V							16		
I_{CEO}	Collector-Emitter Leakage Current at $V_{CE} = 15 \text{ V}$	3041**	nA			500						100
I_{CBO}	Collector-Base Cutoff Current at $V_{CE} = 15 \text{ V}$	3036**	nA			100			500			50
h_{FE}	Forward Current Transfer Ratio HXTR-3001: $V_{CE} = 15 \text{ V}, I_c = 15 \text{ mA}$ HXTR-3101, -3103: $V_{CE} = 10 \text{ V}, I_c = 10 \text{ mA}$	3076*	-	50	100	220	50		180	50		180
f_T	Gain Bandwidth Product at $V_{CE} = 10 \text{ V}, I_c = 15 \text{ mA}$		GHz					6		5.0	7.0	
$ S_{11Z} ^2$	Transducer Gain at $f = 1000 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_c = 15 \text{ mA}$		dB				15.0		13.5	15.0		
NF_{MIN}	Minimum Noise Figure $f = 500 \text{ MHz}$ 1000 MHz 2000 MHz HXTR-3001: $V_{CE} = 10 \text{ V}, I_c = 7 \text{ mA}$ Pkg. Devices: $V_{CE} = 10 \text{ V}, I_c = 10 \text{ mA}$	3246	dB		1.2 1.5 2.2		1.8			1.8	2.3	
$NF_{(50)}$	Noise Figure with $f = 500 \text{ MHz}$ 50 Ohm Source 1000 MHz $V_{CE} = 10 \text{ V}, I_c = 10 \text{ mA}$		dB							1.7 2.1		
MAG	Maximum Available Gain $f = 1000 \text{ MHz}$ 2000 MHz HXTR-3001: $V_{CE} = 15 \text{ V}, I_c = 15 \text{ mA}$ Pkg. Devices: $V_{CE} = 10 \text{ V}, I_c = 15 \text{ mA}$		dB		16.0		19.5					
P_{1dB}	Power Output at $f = 1000 \text{ MHz}$ 1 dB Gain 2000 MHz Compression HXTR-3001: $V_{CE} = 15 \text{ V}, I_c = 25 \text{ mA}$ Pkg. Devices: $V_{CE} = 10 \text{ V}, I_c = 15 \text{ mA}$		dBm		21.0 19.0					16.0		
G_{1dB}	Associated 1 dB Compressed Gain $f = 1000 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_c = 15 \text{ mA}$		dB							16.0		
C_{eb}	Reverse Transfer Capacitance $f = 1 \text{ MHz}$ Capacitance $I_c = 0 \text{ mA}, V_{CE} = 10 \text{ V}$		pF				0.33			0.33		

Notes:

1. $T_A = 25^\circ\text{C}$
2. $T_{CASE} = 25^\circ\text{C}$

^{*}300 μs wide pulse measurement at $\leq 2\%$ duty cycle^{**}Measured under low ambient light conditions, for chip only.

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Electrical Specifications (HSMX-3131, HSMX-3151)

Symbol	Parameters and Test Conditions	Test Method MIL-STD-750	Units	HSMX-3131 ^(u)			HSMX-3151 ^(u)		
				Min.	Typ.	Max.	Min.	Typ.	Max.
BV_{CEO}	Collector-Base Breakdown Voltage at $I_c = 100 \mu A$	3001*	V	25			30		
I_{CEO}	Collector-Base Cutoff Current at $V_{CE} = 15 V$	3036**	nA			500			500
h_{FE}	Forward Current Transfer Ratio HSMX-3131: $V_{CE} = 15 V, I_c = 15 mA$ HSMX-3151: $V_{CE} = 10 V, I_c = 10 mA$	3076*	-	40	80	250	40	80	250
f_T	Gain Bandwidth Product at $V_{CE} = 10 V, I_c = 15 mA$		GHz		6			6	
$ S_{21} ^2$	Transducer Gain at $f = 1000 MHz$ $V_{CE} = 10 V,$ $I_c = 15 mA$		dB		11.3			14.2	
NF_{MIN}	Minimum Noise Figure $f = 1000 MHz$ $2000 MHz$ $V_{CE} = 10 V,$ $I_c = 10 mA$	3246	dB		1.8			2.0 2.5	
G_A	Associated Gain $f = 1000 MHz$ of Minimum Noise Figure, $I_c = 10 mA, V_{CE} = 10 V$		dB					14.9	
MAG	Maximum Available zGain $f = 1000 MHz$ $V_{CE} = 10 V,$ $I_c = 15 mA$		dB		14			19	
P_{1dB}	Power Output at $f = 1000 MHz$ 1 dB Gain $2000 MHz$ Compression $V_{CE} = 10 V, I_c = 15 mA$		dBm		14			17.1 14.6	
G_{1dB}	Associated 1 dB Compressed Gain $f = 1000 MHz$ $2000 MHz$ $V_{CE} = 10 V,$ $I_c = 15 mA$		dB		12			16.0 11.1	
C_{eb}	Reverse Transfer Capacitance $I_c = 0 mA,$ $V_{CE} = 10 V$		pF		0.36			0.36	

^{*}300 μs wide pulse measurement at $\leq 2\%$ duty cycle^{**}Measured under low ambient light conditions, for chip only.

Note:
 1. $T_{CABE} = 25^\circ C$

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Absolute Maximum Ratings*

Symbol	Parameter	HXTR-3001 ⁽¹⁾ (T _A = 25°C)	HXTR-3101/3103 ⁽²⁾ (T _{CASE} = 25°C)	HSMX-3131/3151 ^(3,4) (T _A = 25°C)
V _{CBO}	Collector to Base Voltage	30 V	30 V	25 V
V _{CEO}	Collector to Emitter Voltage	20 V	18 V	15 V
V _{EBO}	Emitter to Base Voltage	1.5 V	1.5 V	1.5 V
I _C	DC Collector Current	70 mA	70 mA	70 mA
P _T	Total Device Dissipation	900 mW	600 mW	250 mW
T _J	Junction Temperature	200°C	200°C	150°C
T _{STG}	Storage Temperature	-65°C to +300°C	-65°C to +150°C	-65°C to +150°C
-	Lead Temperature (Solder-ring 10 seconds each lead)		+250°C	+260°C

*Operation in excess of any one of these conditions may result in permanent damage to this device.

Notes:

- Power dissipation derating should include a θ_{JB} (Junction-to-Back contact thermal resistance) of 65°C/W. Total θ_{JA} (Junction to Ambient) will be dependent upon the heat sinking provided in the individual application.
- A θ_{JC} maximum of 130°C/W should be used for derating and junction temperature calculations ($T_j = P_d \times \theta_{JC} + T_{CASE}$).
- A θ_{JA} of 500°C/C/W should be used for derating and junction temperature calculations ($T_j = P_d \times \theta_{JA} + T_A$).
- Maximum soldering temperature is 260°C for 5 seconds.

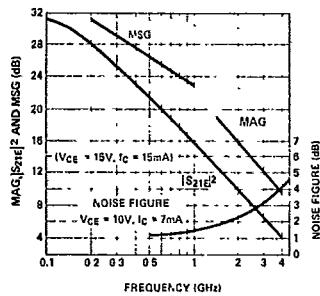


Figure 1. Typical MAG, $|S_{21E}|^2$, Maximum Stable Gain (MSG), and Noise Figure (NF_{MIN}) vs. Frequency for the HXTR-3001.

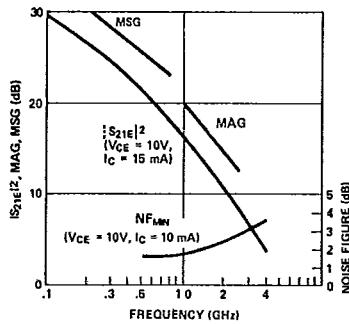


Figure 2. Typical $|S_{21E}|^2$, MAG, Maximum Stable Gain (MSG), and Noise Figure vs. Frequency for the HXTR-3101 and HXTR-3103.

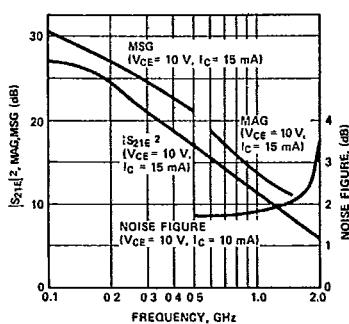


Figure 3. Typical $|S_{21E}|^2$, MAG, MSG, and Noise Figure vs. Frequency for the HSMX-3131.

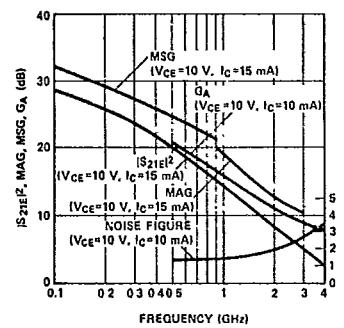


Figure 4. Typical $|S_{21P}|^2$, MAG, MSG, Noise Figure, and G_A vs. Frequency for the HSMX-3151.

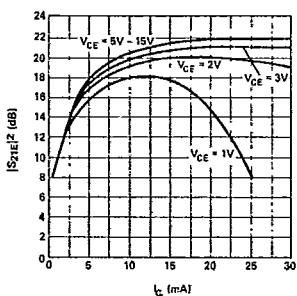


Figure 5. Typical $|S_{21E}|^2$ vs. Collector Current at 500 MHz for the HXTR-3001.

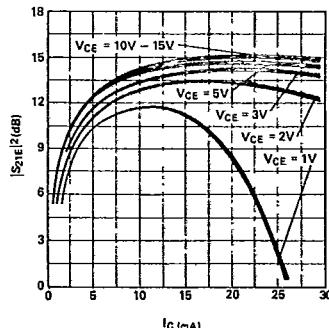


Figure 6. Typical $|S_{21P}|^2$ vs. Collector Current at 1000 MHz for the HXTR-3101 and HXTR-3103.

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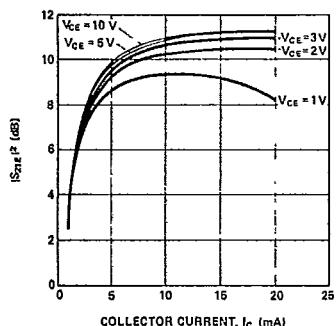


Figure 7. Typical $|S_{21F}|^2$ vs. Collector Current at 1000 MHz for the HSMX-3131.

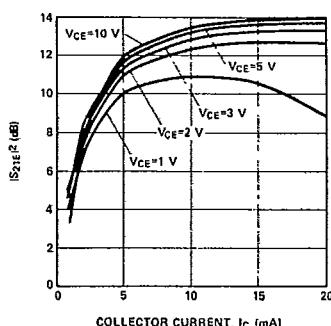


Figure 8. Typical $|S_{21F}|^2$ vs. Collector Current at 1 GHz, for the HSMX-3151.

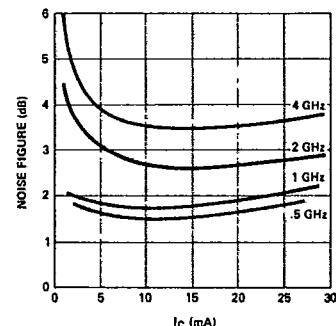


Figure 9. Typical Noise Figure vs. Collector Current ($V_{CE} = 10$ V), for the HXTR-3101.

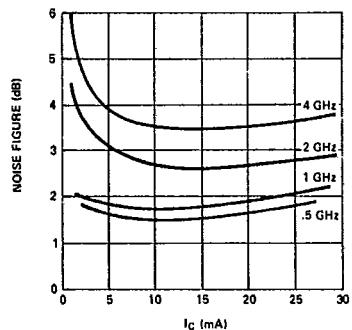


Figure 10. Typical Noise Figure vs. Collector Current for the HXTR-3103.

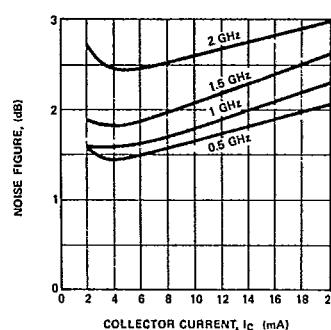


Figure 11. Typical Noise Figure vs. Collector Current ($V_{CE} = 10$ V) for the HSMX-3131.

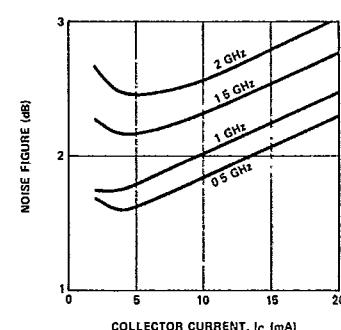


Figure 12. Typical Noise Figure vs. Collector Current, $V_{CE} = 10$ V, for the HSMX-3151.

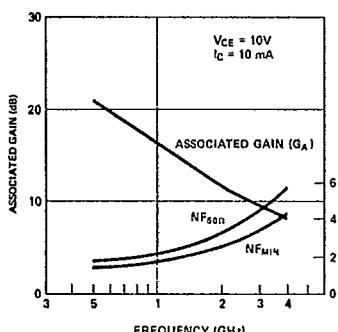


Figure 13. Typical Noise Figure vs. Frequency for the HXTR-3103.

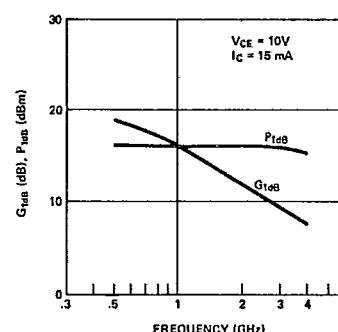


Figure 14. Typical Power Output at 1 dB Gain Compression vs. Frequency for the HXTR-3103.

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Typical Noise Parameters ($V_{CE} = 10$ V, $I_C = 10$ mA)**HXTR-3103**

Freq. (GHz)	NF _{MIN} (dB)	Γ_o		R _N (Ohms)
		Mag.	Angle	
0.5	1.4	0.121	96	114.4
1.0	1.7	0.301	121	15.2
2.0	2.5	0.461	173	5.2
3.0	3.3	0.553	-157	8.4
4.0	4.2	0.648	-139	13.4

**HSMX-3131**

Freq. (GHz)	NF _{MIN} (dB)	G _A dB	Γ_o Source		Γ_L Load		R _N (Ohms)
			Mag.	Angle	Mag.	Angle	
0.5	1.7	18.2	0.36	-10	0.36	-25	60
1.0	1.8	12.5	0.45	-130	0.20	1.09	2
1.5	2.1	9.7	0.32	31	0.30	-87	7
2.0	3.3	5.6	0.50	-171	0.96	67	10

HSMX-3151

Freq. (GHz)	NF _{MIN} (dB)	G _A dB	Γ_o Source		Γ_L Load		R _N (Ohms)
			Mag.	Angle	Mag.	Angle	
0.5	1.9	20.0	0.07	91	0.52	15	19
1.0	2.0	14.9	0.23	127	0.56	35	9
1.5	2.3	12.2	0.39	145	0.63	53	5
2.0	2.5	10.7	0.36	180	0.54	62	10

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HXTR-3001 Typical Common Emitter S-Parameters ($V_{CE} = 15$ V, $I_C = 15$ mA)*

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.651	-74	30.6	34.04	146	-37.2	0.014	59
200	0.714	-113	27.8	24.66	125	-33.9	0.020	43
300	0.741	-132	25.3	18.41	114	-32.9	0.023	36
400	0.754	-143	23.2	14.46	107	-32.3	0.024	33
500	0.761	-151	21.5	11.84	102	-32.0	0.025	31
600	0.765	-155	20.0	10.00	98	-31.7	0.026	32
700	0.767	-159	18.7	8.63	95	-31.5	0.027	32
800	0.768	-162	17.6	7.59	93	-31.2	0.028	33
900	0.769	-164	16.6	6.77	91	-31.0	0.028	34
1000	0.770	-166	15.7	6.11	89	-30.7	0.029	35
1500	0.770	-171	12.2	4.10	81	-29.3	0.034	41
2000	0.769	-174	9.8	3.06	74	-28.0	0.040	44
2500	0.766	-176	7.8	2.46	69	-26.8	0.046	47
3000	0.763	-177	6.2	2.05	63	-25.7	0.052	48
3500	0.760	-178	4.9	1.75	58	-24.7	0.058	48
4000	0.756	-179	3.7	1.53	53	-23.8	0.064	48

*Values do not include any parasitic bonding inductances and were generated by use of a computer model.

RF Equivalent Circuit See page 3-7.

HXTR-3101/3103 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 10$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.70	-50	27.7	24.26	149	-36.7	0.015	60
200	0.64	-86	25.6	19.05	129	-32.2	0.025	49
300	0.60	-110	23.5	14.96	116	-30.4	0.030	43
400	0.57	-127	21.6	12.02	108	-29.6	0.033	41
500	0.56	-139	20.1	10.11	102	-28.9	0.036	41
600	0.55	-149	18.7	8.61	97	-28.5	0.038	42
700	0.56	-157	17.5	7.49	93	-27.9	0.040	43
800	0.55	-162	16.5	6.68	89	-27.4	0.043	44
900	0.55	-168	15.5	5.95	85	-26.9	0.045	46
1000	0.57	-169	14.5	5.33	78	-25.7	0.052	42
1500	0.57	174	11.2	3.62	63	-23.6	0.066	48
2000	0.59	162	8.9	2.77	49	-21.9	0.080	48
2500	0.61	153	7.2	2.28	37	-20.4	0.096	48
3000	0.61	143	5.7	1.93	25	-18.8	0.115	45
3500	0.65	134	4.5	1.67	13	-17.5	0.134	43
4000	0.63	125	3.5	1.48	1	-16.2	0.155	39

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HXTR-3101/3103 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 15$ mA)

Freq. (MHz)	S_{11}		S_{21}			S_{12}		S_{22}		
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.	Mag.	Ang.
100	0.64	-60	29.5	29.85	144	-37.6	0.013	57	0.86	-24
200	0.58	-98	26.9	22.13	124	-33.4	0.021	47	0.67	-34
300	0.56	-122	24.5	16.78	112	-31.8	0.026	44	0.55	-38
400	0.54	-138	22.4	13.18	104	-30.9	0.029	43	0.48	-39
500	0.54	-149	20.7	10.83	98	-30.1	0.031	44	0.44	-40
600	0.53	-157	19.3	9.22	94	-29.5	0.033	47	0.41	-40
700	0.54	-164	18.1	8.03	90	-28.7	0.037	49	0.39	-41
800	0.54	-168	17.1	7.16	87	-28.1	0.039	50	0.38	-41
900	0.54	-173	16.1	6.38	84	-27.4	0.043	52	0.37	-42
1000	0.56	-175	15.1	5.70	77	-26.4	0.048	49	0.36	-39
1500	0.56	-171	11.8	3.86	62	-23.6	0.066	54	0.35	-47
2000	0.58	-159	9.4	2.95	49	-21.6	0.083	52	0.35	-56
2500	0.61	-151	7.7	2.42	38	-20.0	0.100	51	0.35	-70
3000	0.61	-142	6.3	2.05	26	-18.4	0.120	47	0.38	-81
3500	0.64	-133	5.0	1.78	14	-17.1	0.139	44	0.38	-94
4000	0.63	-124	4.0	1.58	2	-15.9	0.160	39	0.43	-106

HSMX-3131 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 5$ mA)

Freq. (MHz)	S_{11}		S_{21}			S_{12}		S_{22}		
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.	Mag.	Ang.
100	0.77	-31	21.6	11.95	154	-32.5	0.024	154	0.93	-14
200	0.65	-55	20.0	10.03	135	-28.1	0.039	135	0.82	-21
300	0.53	-75	18.3	8.22	121	-26.0	0.050	121	0.73	-26
400	0.45	-91	16.7	6.80	110	-24.7	0.058	110	0.66	-28
500	0.39	-104	15.2	5.74	102	-23.7	0.065	102	0.62	-29
600	0.34	-116	13.9	4.93	96	-22.8	0.072	96	0.59	-29
700	0.31	-126	12.7	4.33	90	-22.0	0.079	90	0.58	-30
800	0.29	-135	11.7	3.85	85	-21.3	0.086	85	0.56	-31
900	0.27	-144	10.8	3.45	81	-20.6	0.094	81	0.56	-33
1000	0.26	-152	10.0	3.14	77	-19.9	0.102	77	0.55	-34
1100	0.25	-159	9.2	2.89	73	-19.2	0.110	73	0.55	-35
1200	0.25	-166	8.6	2.68	70	-18.5	0.118	70	0.55	-36
1300	0.24	-172	8.0	2.50	67	-17.9	0.127	67	0.54	-38
1400	0.24	-179	7.4	2.45	64	-17.3	0.136	64	0.55	-39
1500	0.23	176	6.9	2.21	61	-16.7	0.146	61	0.55	-41
2000	0.23	148	4.8	1.73	47	-14.0	0.199	47	0.55	-49

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HSMX-3131 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 10$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.62	-43	25.4	18.69	144	-33.5	0.021	71
200	0.47	-70	22.9	13.91	124	-29.6	0.033	65
300	0.36	-91	20.4	10.42	110	-27.3	0.043	64
400	0.30	-107	18.3	8.22	102	-25.7	0.052	66
500	0.26	-119	16.6	6.75	95	-24.3	0.061	67
600	0.23	-130	15.1	5.72	90	-23.1	0.070	68
700	0.22	-140	13.9	4.97	86	-22.0	0.079	69
800	0.20	-149	12.8	4.39	81	-21.0	0.089	70
900	0.19	-157	11.9	3.92	78	-20.1	0.099	70
1000	0.19	-164	11.0	3.56	74	-19.3	0.109	71
1100	0.18	-171	10.3	3.27	71	-18.5	0.119	71
1200	0.18	-178	9.6	3.02	68	-17.8	0.129	71
1300	0.18	177	9.0	2.81	65	-17.2	0.139	71
1400	0.18	171	8.4	2.63	62	-16.5	0.149	71
1500	0.17	165	7.9	2.47	60	-15.9	0.160	70
2000	0.18	140	5.7	1.93	47	-13.3	0.215	68

HSMX-3131 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 15$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.54	-51	27.0	22.50	138	-34.2	0.020	70
200	0.38	-80	23.8	15.51	118	-30.4	0.030	67
300	0.29	-101	21.0	11.18	105	-27.9	0.040	68
400	0.24	-117	18.8	8.67	98	-26.1	0.050	70
500	0.21	-129	17.0	7.06	92	-24.5	0.059	71
600	0.19	-140	15.5	5.94	87	-23.2	0.070	72
700	0.18	-150	14.2	5.14	83	-22.0	0.080	72
800	0.17	-158	13.1	4.54	80	-20.9	0.090	73
900	0.17	-166	12.2	4.05	76	-20.0	0.100	73
1000	0.16	-173	11.3	3.67	73	-19.1	0.111	73
1100	0.16	-179	10.5	3.36	70	-18.3	0.121	73
1200	0.16	175	9.8	3.11	67	-17.6	0.132	72
1300	0.16	170	9.2	2.89	64	-16.9	0.143	72
1400	0.16	164	8.6	2.70	62	-16.3	0.153	71
1500	0.16	159	8.1	2.54	59	-15.7	0.164	71

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HSMX-3151 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 5$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.73	-31	21.8	12.31	160	-34.9	0.018	71
200	0.68	-59	20.7	10.89	144	-29.9	0.032	62
300	0.65	-82	19.6	9.52	130	-27.7	0.041	53
400	0.63	-101	18.4	8.27	120	-26.4	0.048	45
500	0.61	-116	17.2	7.21	111	-25.8	0.051	41
600	0.60	-127	16.0	6.30	104	-25.4	0.054	40
700	0.59	-137	14.9	5.57	99	-25.0	0.056	38
800	0.58	-145	13.9	4.98	93	-24.7	0.058	38
900	0.58	-152	13.0	4.49	89	-24.6	0.059	37
1000	0.58	-158	12.2	4.07	85	-24.3	0.061	37
1100	0.58	-164	11.5	3.75	81	-24.2	0.062	38
1200	0.58	-168	10.8	3.48	77	-23.9	0.064	38
1300	0.58	-173	10.1	3.21	74	-24.0	0.063	38
1400	0.58	-177	9.5	2.99	71	-23.7	0.065	40
1500	0.58	180	9.0	2.82	68	-23.7	0.066	41
2000	0.59	165	6.6	2.14	54	-22.4	0.076	47
2500	0.59	152	4.7	1.72	43	-21.2	0.087	53
3000	0.60	140	3.2	1.45	32	-19.6	0.105	56
3500	0.61	129	2.0	1.25	22	-18.0	0.126	57
4000	0.63	118	0.8	1.10	12	-16.4	0.152	56

HSMX-3151 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 10$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.60	-48	26.2	20.30	153	-35.6	0.017	68
200	0.56	-84	24.3	16.39	134	-31.6	0.026	56
300	0.55	-110	22.5	13.26	120	-29.7	0.033	50
400	0.55	-127	20.7	10.86	110	-28.8	0.036	47
500	0.55	-140	19.2	9.08	102	-28.3	0.038	46
600	0.55	-149	17.8	7.78	97	-27.6	0.042	45
700	0.55	-156	16.6	6.78	92	-27.2	0.044	46
800	0.55	-163	15.6	6.00	87	-26.7	0.046	48
900	0.55	-168	14.6	5.36	84	-26.5	0.047	47
1000	0.55	-172	13.7	4.86	80	-25.7	0.052	49
1100	0.55	-176	12.9	4.42	77	-25.4	0.054	48
1200	0.55	-180	12.3	4.11	74	-25.2	0.055	52
1300	0.55	177	11.5	3.78	71	-24.5	0.059	53
1400	0.55	173	10.9	3.52	68	-24.1	0.062	53
1500	0.56	171	10.4	3.30	65	-23.8	0.064	55
2000	0.56	158	8.0	2.50	53	-21.9	0.081	58
2500	0.57	147	6.1	2.02	42	-20.2	0.098	60
3000	0.57	136	4.6	1.69	32	-18.4	0.120	58
3500	0.58	126	3.3	1.47	22	-17.0	0.141	58
4000	0.60	115	2.2	1.29	13	-15.5	0.168	56

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HSMX-3151 Typical Common Emitter S-Parameters ($V_{CE} = 10$ V, $I_C = 15$ mA)

Freq. (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
	Mag.	Ang.	(dB)	Mag.	Ang.	(dB)	Mag.	Ang.
100	0.53	-61	28.1	25.42	148	-36.6	0.015	64
200	0.52	-101	25.7	19.21	128	-32.9	0.023	55
300	0.53	-125	23.4	14.86	114	-31.2	0.028	50
400	0.54	-141	21.5	11.83	105	-30.3	0.031	50
500	0.54	-151	19.8	9.73	98	-29.6	0.033	50
600	0.54	-159	18.4	8.28	93	-28.7	0.027	51
700	0.54	-165	17.1	7.17	89	-28.1	0.039	52
800	0.54	-170	16.0	6.32	85	-27.6	0.042	55
900	0.54	-175	15.0	5.64	82	-27.1	0.044	55
1000	0.55	-178	14.2	5.11	78	-26.2	0.049	56
1100	0.55	178	13.3	4.64	75	-25.9	0.051	54
1200	0.55	175	12.6	4.29	72	-25.5	0.053	58
1300	0.55	172	11.9	3.94	69	-24.7	0.058	59
1400	0.55	169	11.3	3.67	67	-24.3	0.061	59
1500	0.55	167	10.8	3.45	64	-23.9	0.064	61
2000	0.56	155	8.3	2.60	53	-21.7	0.082	63
2500	0.56	145	6.4	2.10	42	-19.9	0.101	63
3000	0.57	134	4.9	1.76	31	-18.1	0.124	60
3500	0.58	124	3.6	1.52	22	-16.8	0.145	59
4000	0.59	113	2.5	1.34	13	-15.3	0.173	57

Ordering Information

See page 16-2 for information on ordering surface mount devices.

High Reliability Testing*

Two basic levels of High-Reliability testing are offered.

1. The TX suffix indicates a part that is preconditioned and screened to the program shown in Table II and III, and is marked with an orange dot.

2. The TXV suffix indicates that an internal visual inspection per MIL-STD-750 Method 2072 is included as part of the preconditioning screening and is marked with a green dot.

Group B quality conformance inspections are performed on

Part Number System for Order and RFQ Information

Part Number Prefix	Screening Level
HXTR-3101 2N6838 (HXTR-3103)	Commercial
HXTR-3101TX 2N6838TX (HXTR-3101TX)	100% Screen (per Tables II and III)
HXTR-3101TXV 2N6838TXV (HXTR-3103TXV)	100% Screen and Internal Visual

each inspection lot in accordance with Table IVb. Group C quality conformance inspections are performed periodically at six month intervals in accordance with Table V.

*Please refer to MIL-S-19500 for Tables II, III, IVb, and V. High power visual performed on die prior to assembly.

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100% Screen	Screened per MIL-S-19500, Table II, TX or TXV with the following specified tests and conditions:	
	HTRB Test (Screen 10)*	Delete HTRB
	Pre Burn In Tests (Screen 11)*	All DC parameters; BV_{CBO} , BV_{CEO} , I_{CBO} , I_{CEO} and h_{FE} at $25^\circ C$, per data sheet Electrical Specifications table
	Burn In Conditions (Screen 12)*	$P_T = 300 \text{ mW}$, $T_A = 25^\circ C$
	Post Burn In Tests (Screen 13)*	HXTR-3101 All DC parameters; BV_{CBO} , I_{CBO} , I_{CEO} , and h_{FE} at $25^\circ C$, per data sheet Electrical Specifications table
		HXTR-3103 All DC parameters; BV_{CBO} , BV_{CEO} , I_{CBO} , I_{CEO} , and h_{FE} at $25^\circ C$, per data sheet Electrical Specifications table
Group A	Per MIL-S-19500, Table III, and the following:	
	Subgroup 2	HXTR-3101 BV_{CEO} , I_{CBO} , I_{CEO} and h_{FE} at $25^\circ C$ per data sheet Electrical Specifications table
		HXTR-3103 BV_{CBO} , BV_{CEO} , I_{CBO} , I_{CEO} and h_{FE} at $25^\circ C$ per data sheet Electrical Specifications table
	Subgroup 3	$T_A = +150^\circ C$, $I_{CBO} = 5 \mu\text{A}$ at $V_{CB} = 15 \text{ V}$ $T_A = -55^\circ C$, $h_{FE} = 20$ minimum at $I_C = 10 \text{ mA}$, $V_{CE} = 10 \text{ V}$
	Subgroup 4	HXTR-3101 Not applicable
		HXTR-3103 f_T , $ S_{21B} ^2$ and NF_{MIN} per data sheet Electrical Specifications table
	Subgroups 5, 6, and 7 are not applicable.	
Group B	Per MIL-S-19500, Table IVb. End point tests per Group A Subgroup 2, with the following conditions and exceptions:	
	Subgroup 3	Operating Life conditions same as 100% burn-in.
	except Subgroup 4	SEM, done prior to assembly
	except Subgroup 5	Thermal resistance, per MIL-STD-750 Method 3151
Group C	Per MIL-S-19500, Table V. No exceptions. End point tests per Group A Subgroup 2, and with the following conditions:	
	Subgroup 6	Operating Life conditions same as 100% burn-in.

*Refer to MIL-S-19500 screen numbers.

